Ordering number: EN2973

PNP Epitaxial Planar Silicon Transistors



2SA1699

High-Voltage Driver Applications

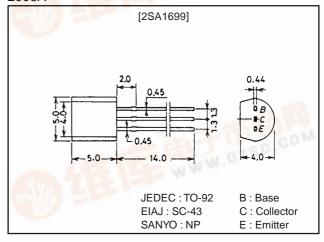
Features

- · High breakdown voltage.
- · Adoption of MBIT process.
- · Excellent h_{FE} linearity.

Package Dimensions

unit:mm

2003A



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		-400	V
Collector-to-Emitter Voltage	V _{CEO}		-400	V
Emitter-to-Base Voltage	V _{EBO}		-5	V
Collector Current	IC		-200	mA
Colletor Current (Pulse)	ICP	_ / ET \T-	-400	mA
Collector Dissipation	PC	478 7 12	600	mW
Junction Temperature	Tj	951//6	150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
		Conditions		typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =-300V, I _E =0			-0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
DC Current Gain	h _{FE}	V _{CE} =-10V, I _C =-50mA	60*	4	200*	
Gain-Bandwidth Product	fT	V _{CE} =-30V, I _C =-10mA		70	40-1	MHz
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-50mA, I _B =-5mA		M.D.	-0.8	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-50mA, I _B =-5mA			-1.0	V

Continued on next page.

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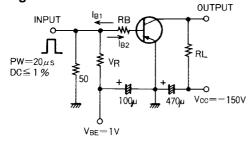
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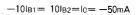
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol	Conditions		typ	max	Onit
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =-10μA, I _E =0	-400			V
Collector-to-Emitter Breakdown Voltage	V _(BR) CEO	I _C =-1mA, R _{BE} =∞	-400			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =-10μA, I _C =0	-5			V
Collector Output Capacitance	C _{ob}	V _{CB} =–30V, f=1MHz		5		pF
Reverse Trarnsfer Capacitance	C _{re}	V _{CB} =–30V, f=1MHz		4		pF
Turn-ON Time	ton	See specified Test Circuit		0.25		μs
Turn-OFF Time	t _{off}	See specified Test Circuit		5		μs

 $[\]mbox{\ast}$: The 2SA1699 is classified by 50mA \mbox{h}_{FE} as follows :

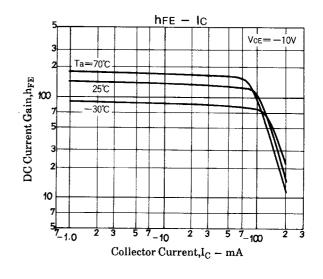
60	D	120	100	Е	200	

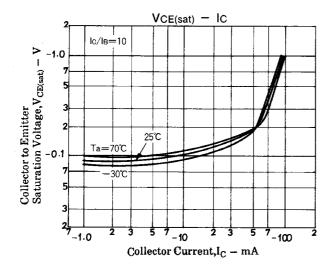
Switching Time Test Circuit

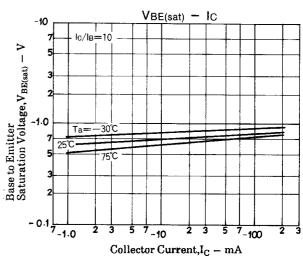


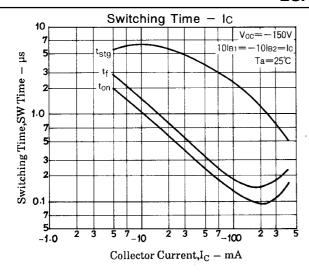


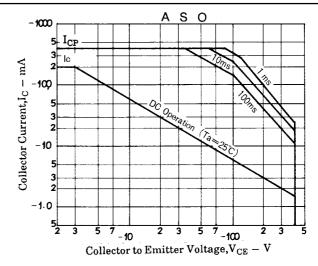
 $R_L = 3k\Omega$, $R_B = 200\Omega$ at $I_C = -50mA$ Unit (resistance : Ω , capacitance : F) -120 $V_{CE} = -10V$ 33. -100 Collector Current, Ic - mA -80 -60 -40 -20 0 -0.6 0 -0.4 -0.8 -1.0 -1.2 Base to Emitter Voltage, $V_{BE} - V$

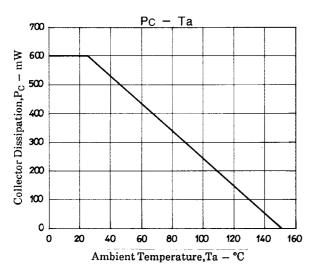












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